30V N+P Dual Channel MOSFETs

PDC3707CV

General Description

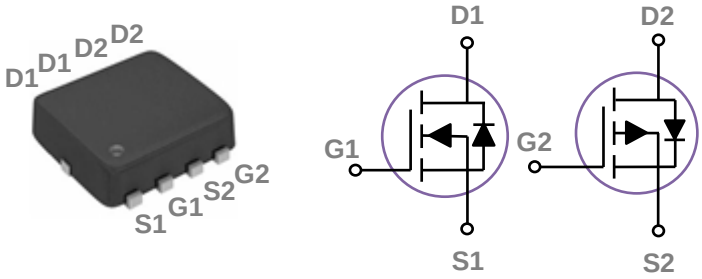
These N+P dual Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
30V	11.5mΩ	30A
-30V	23mΩ	-25A

Features

- *Fast switching*
- *Green Device Available*
- *100% EAS Guaranteed*

PPAK3X3 Dual Pin Configuration



Applications

- *DC Fan*
- *Motor Drive Applications*
- *Networking*
- *Half / Full Bridge Topology*

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating		Units
V_{DS}	Drain-Source Voltage	30	-30	V
V_{GS}	Gate-Source Voltage	±20	±20	V
I_D	Drain Current – Continuous (T_C=25℃)	30	-25	A
	Drain Current – Continuous (T_C=100℃)	19	-16	A
I_{DM}	Drain Current – Pulsed[1]	120	-100	A
EAS	Single Pulse Avalanche Energy[2,6]	20	45	mJ
IAS	Single Pulse Avalanched Current[2]	20	-30	A
P_D	Power Dissipation (T_C=25℃)	22		W
	Power Dissipation – Derate above 25℃	0.18		W/℃
T_{STG}	Storage Temperature Range	-55 to 150		℃
T_J	Operating Junction Temperature Range	-55 to 150		℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	5.6	℃/W

N-CH Electrical Characteristics (T_J=25 ℃, unless otherwise)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=30V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=24V , V_{GS}=0V , T_J=125℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=8A	---	9.5	11.5	mΩ
		V_{GS}=4.5V , I_D=5A	---	12	16	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	1.5	2.5	V
gfs	Forward Transconductance	V_{DS}=10V , I_D=5A	---	5	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[3,4]	V_{DS}=15V , V_{GS}=10V , I_D=15A	---	11.5	18	nC
Q_{gs}	Gate-Source Charge[3,4]		---	1.3	3	
Q_{gd}	Gate-Drain Charge[3,4]		---	3.2	5	
$T_{d(on)}$	Turn-On Delay Time[3,4]	V_{DD}=15V , V_{GS}=10V , R_G=6Ω , I_D=15A	---	4	6	ns
T_r	Rise Time[3,4]		---	10	15	
$T_{d(off)}$	Turn-Off Delay Time[3,4]		---	22	33	
T_f	Fall Time[3,4]		---	7	11	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , F=1MHz	---	720	1080	pF
C_{oss}	Output Capacitance		---	100	150	
C_{rss}	Reverse Transfer Capacitance		---	85	130	
Rg	Gate resistance	V_{GS}=0V, V_{DS}=0V, F=1MHz	---	2.7	---	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	30	A
I_{SM}	Pulsed Source Current		---	---	60	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1	V
t_{rr}	Reverse Recovery Time	V_R=30V, I_S=10A , di/dt=100A/μs, T_J=25℃	---	110	---	ns
Q_{rr}	Reverse Recovery Charge		---	140	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=20A.,R_G=25Ω,Starting T_J=25℃.
3. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
4. Essentially independent of operating temperature.

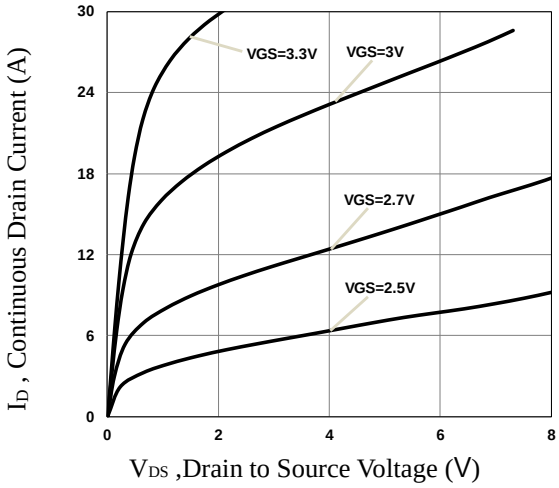


Fig.1 Typical Output Characteristics

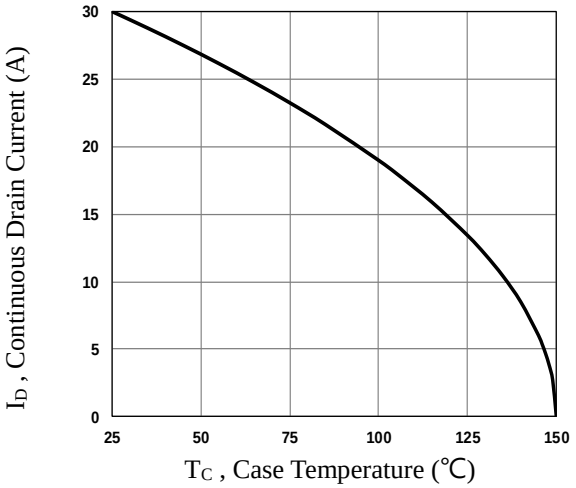


Fig.2 Continuous Drain Current vs. T_C

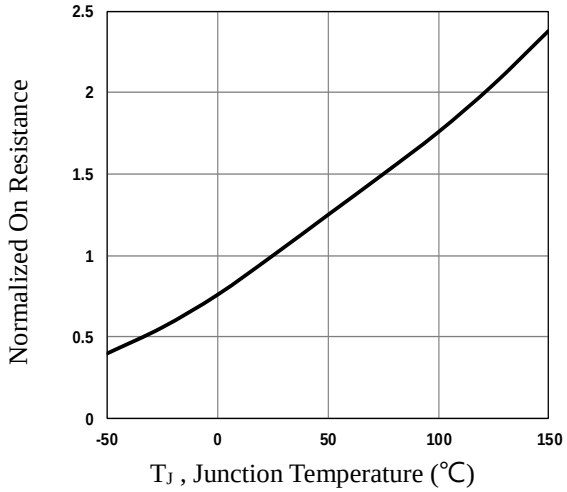


Fig.3 Normalized RDSON vs. T_J

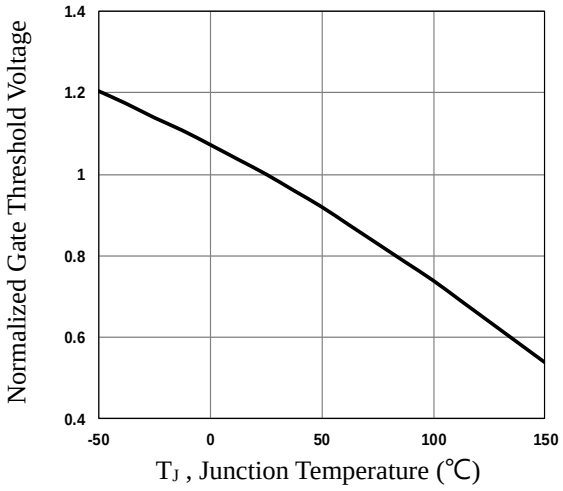


Fig.4 Normalized V_{th} vs. T_J

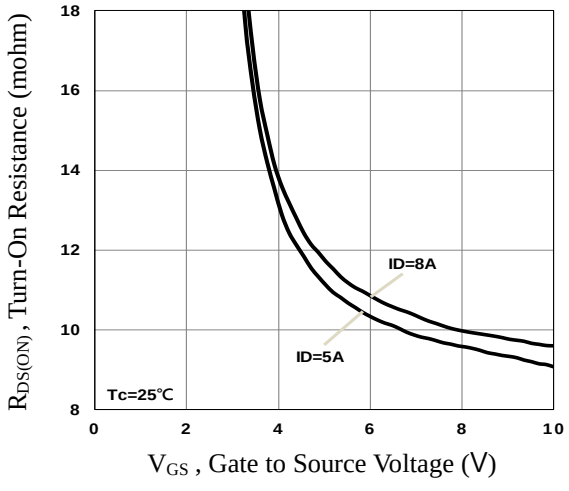


Fig.5 Turn-On Resistance vs. V_{GS}

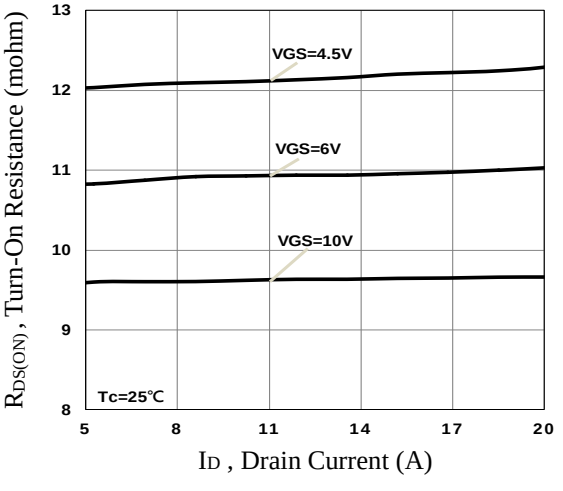


Fig.6 Turn-On Resistance vs. ID

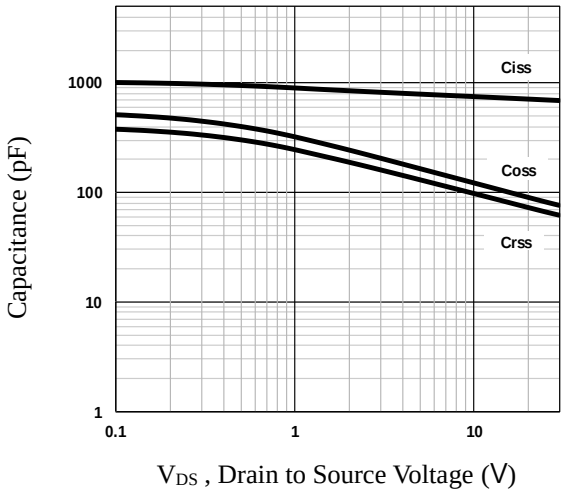


Fig.7 Capacitance Characteristics

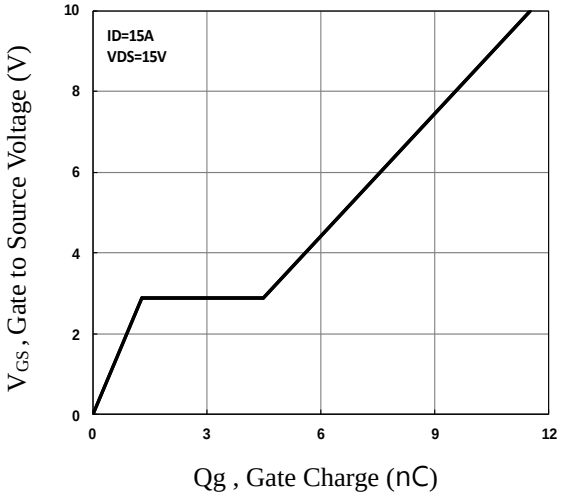


Fig.8 Gate Charge Characteristics

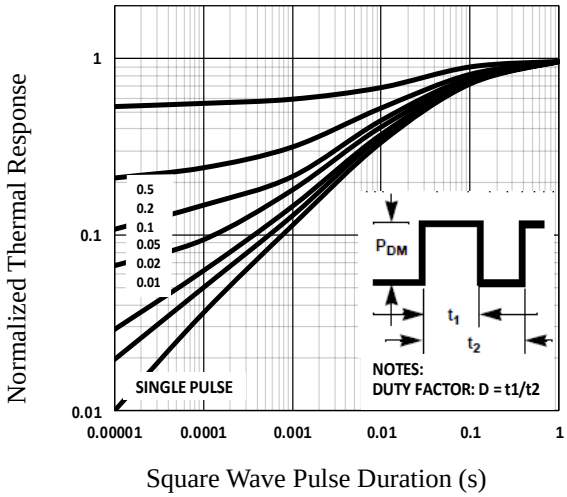


Fig.9 Normalized Transient Impedance

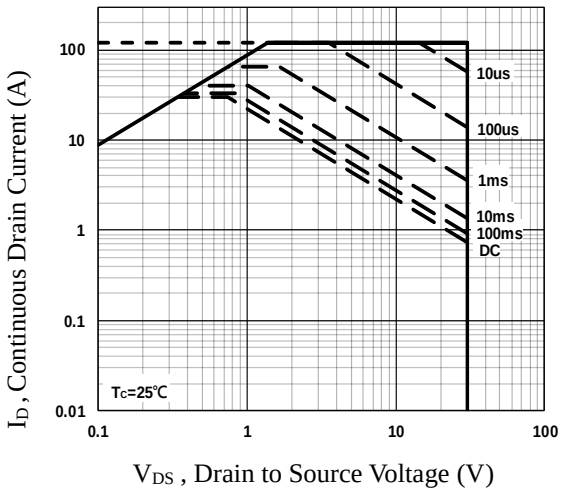


Fig.10 Maximum Safe Operation Area

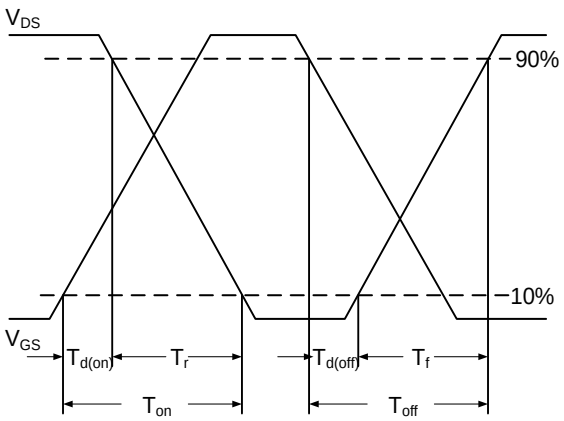


Fig.11 Switching Time Waveform

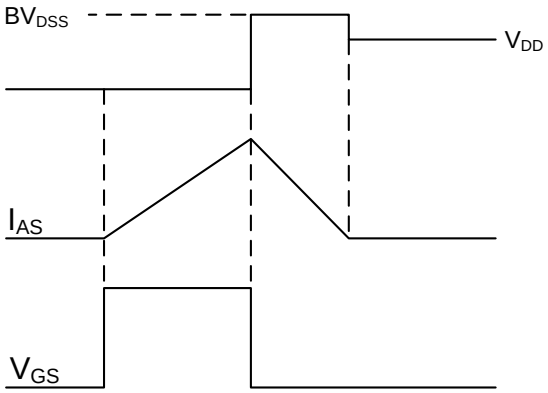


Fig.12 EAS Waveform

P-CH Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-30	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-30V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-24V , V_{GS}=0V , T_J=125℃	---	---	-10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V , I_D=-8A	---	19	23	mΩ
		V_{GS}=-4.5V , I_D=-5A	---	29	35	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.2	-1.5	-2.5	V
gfs	Forward Transconductance	V_{DS}=-10V , I_D=-3A	---	4	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[7,8]	V_{DS}=-15V , V_{GS}=-10V , I_D=-15A	---	18.5	28	nC
Q_{gs}	Gate-Source Charge[7,8]		---	2.5	4	
Q_{gd}	Gate-Drain Charge[7,8]		---	4.3	7	
$T_{d(on)}$	Turn-On Delay Time[7,8]	V_{DD}=-15V , V_{GS}=-10V , R_G=6Ω , I_D=-15A	---	7.2	11	ns
T_r	Rise Time[7,8]		---	38	57	
$T_{d(off)}$	Turn-Off Delay Time[7,8]		---	34	51	
T_f	Fall Time[7,8]		---	8.2	12	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , F=1MHz	---	1100	1650	pF
C_{oss}	Output Capacitance		---	175	260	
C_{rss}	Reverse Transfer Capacitance		---	130	195	
Rg	Gate resistance	V_{GS}=0V, V_{DS}=0V, F=1MHz	---	13	---	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	-25	A
I_{SM}	Pulsed Source Current		---	---	-50	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1	V
t_{rr}	Reverse Recovery Time	V_R=-30V, I_S=-10A , di/dt=100A/μs, T_J=25℃	---	150	---	ns
Q_{rr}	Reverse Recovery Charge		---	260	---	nC

Note :

5. Repetitive Rating : Pulsed width limited by maximum junction temperature.
6. V_{DD}=-25V,V_{GS}=-10V,L=0.1mH,I_{AS}=-30A.,R_G=25Ω,Starting T_J=25℃
7. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
8. Essentially independent of operating temperature.

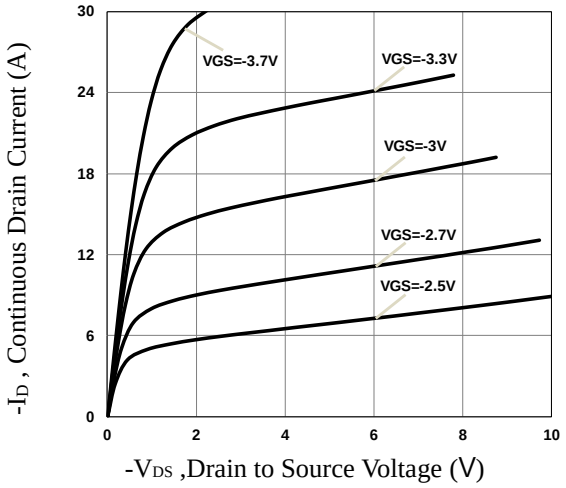


Fig.13 Typical Output Characteristics

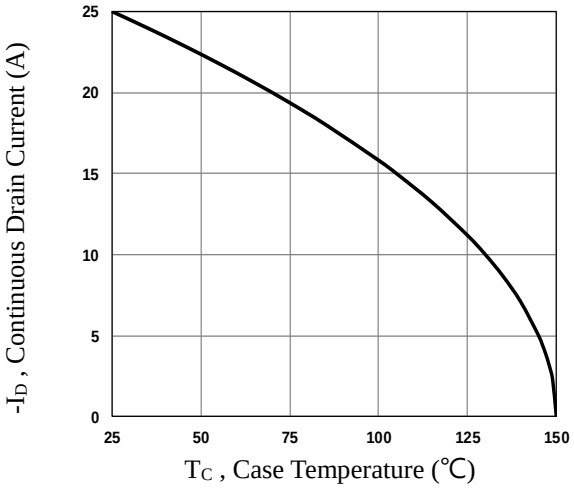


Fig.14 Continuous Drain Current vs. T_C

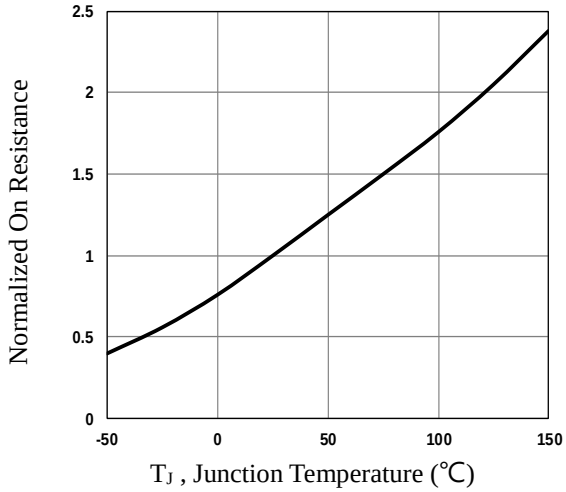


Fig.15 Normalized RDSON vs. T_J

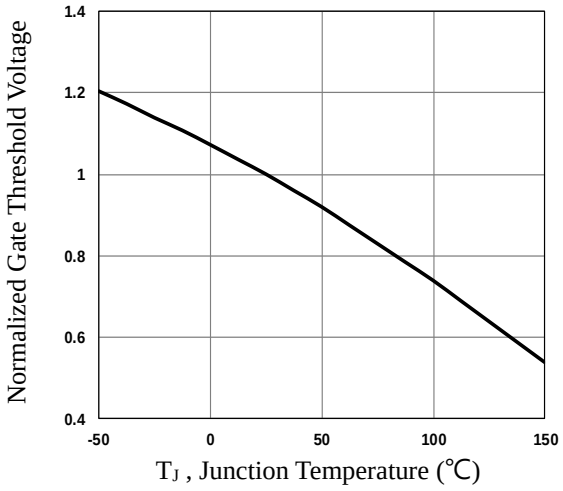


Fig.16 Normalized V_{th} vs. T_J

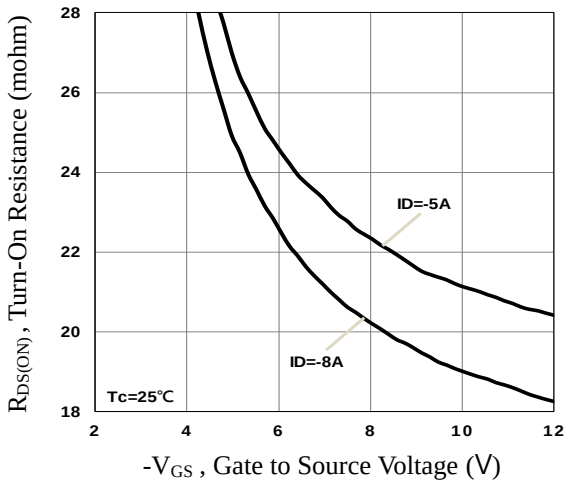


Fig.17 Turn-On Resistance vs. V_{GS}

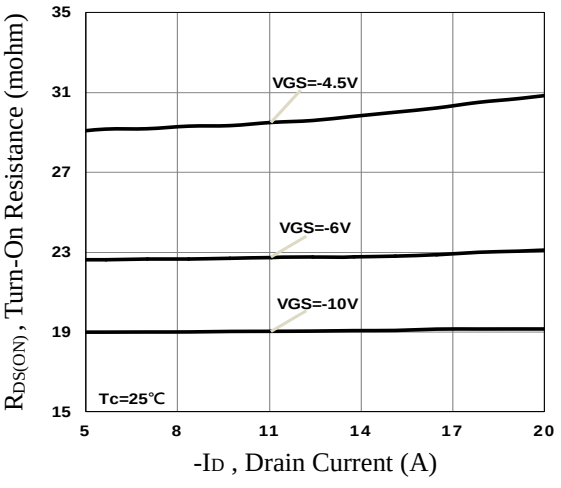


Fig.18 Turn-On Resistance vs. I_D

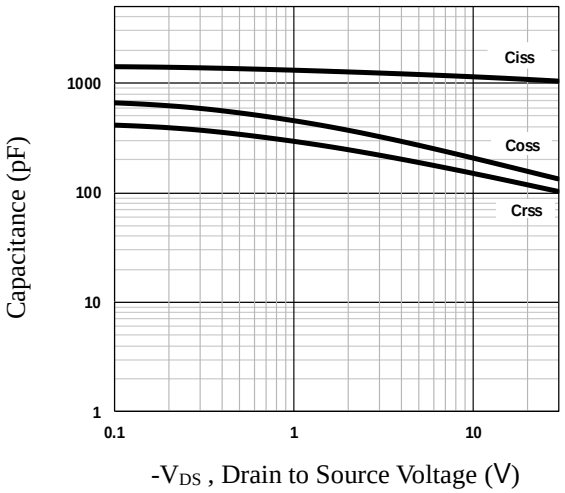


Fig.19 Capacitance Characteristics

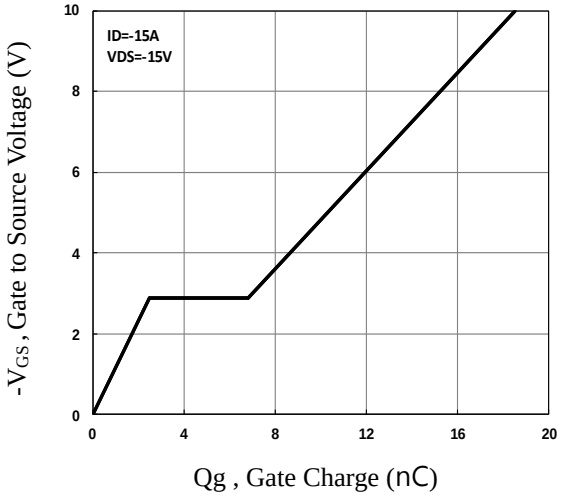


Fig.20 Gate Charge Characteristics

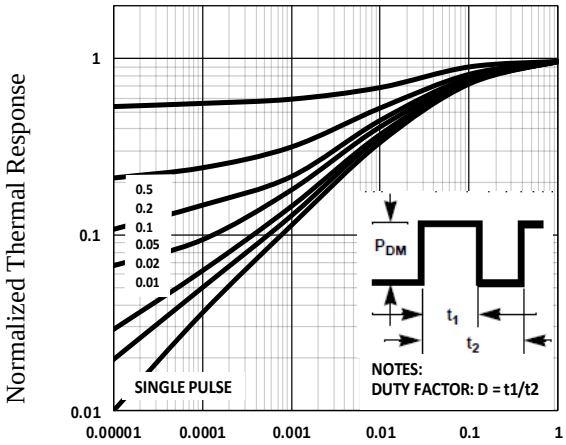


Fig.21 Normalized Transient Impedance

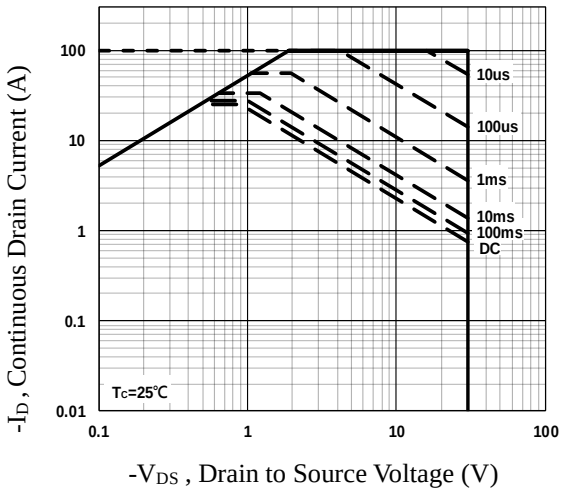


Fig.22 Maximum Safe Operation Area

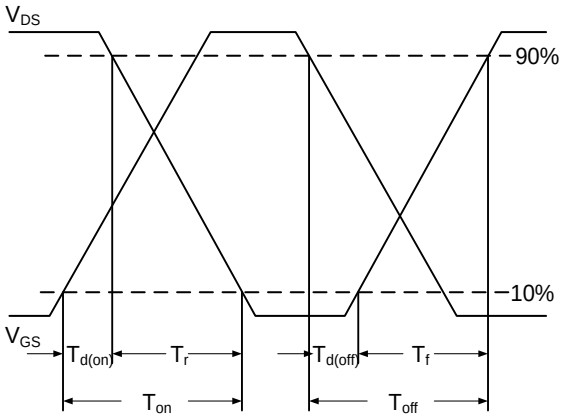


Fig.23 Switching Time Waveform

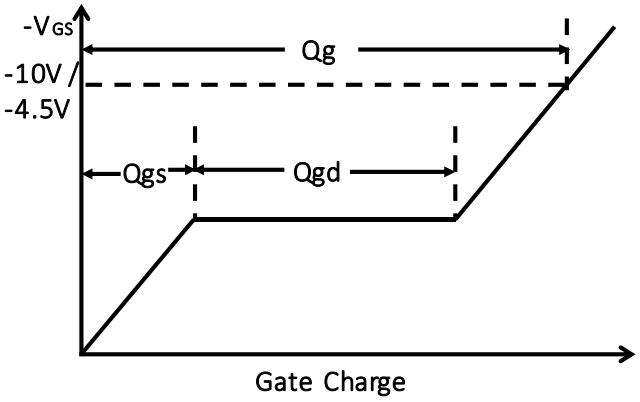
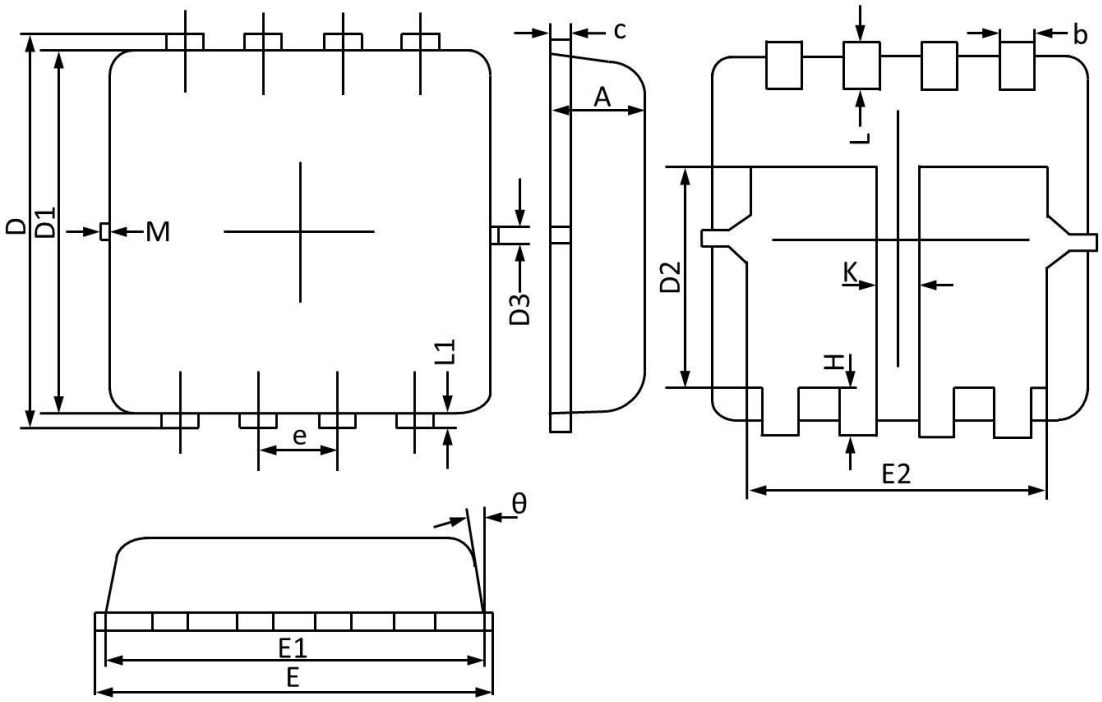


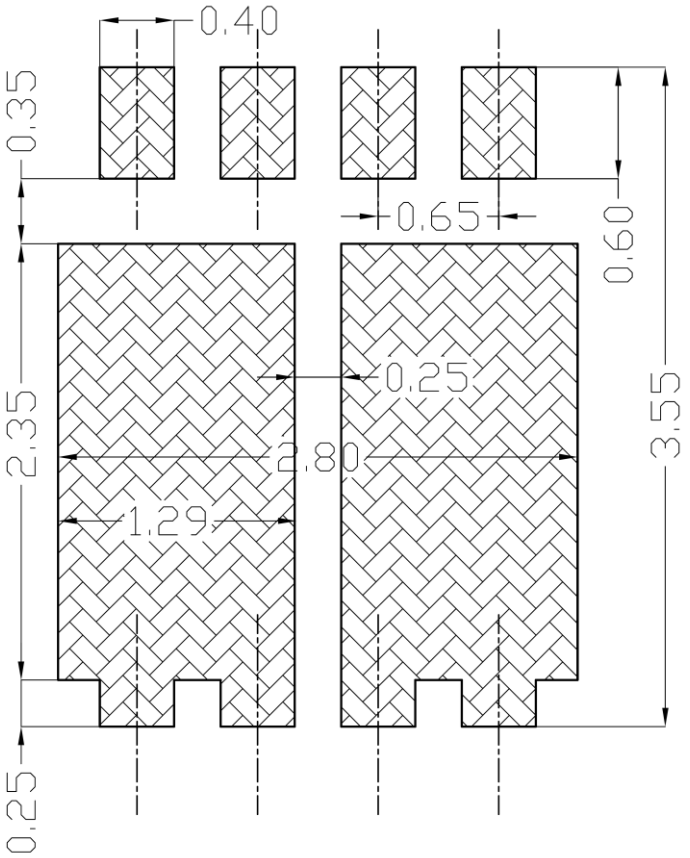
Fig.24 Gate Charge Waveform

PPAK3x3 Dual PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.670	0.880	0.026	0.035
b	0.250	0.350	0.010	0.014
c	0.100	0.250	0.004	0.010
D	3.150	3.550	0.124	0.140
D1	3.000	3.300	0.118	0.130
D2	1.500	2.000	0.059	0.079
D3	0.130	0.200	0.005	0.008
E	3.100	3.500	0.122	0.138
E1	3.000	3.200	0.118	0.126
E2	2.350	2.600	0.093	0.102
e	0.650 BSC		0.026 BSC	
H	0.300	0.500	0.012	0.020
L	0.300	0.500	0.012	0.020
L1	0.130 REF		0.005 REF	
K	0.300 REF		0.012 REF	
θ	0°	12°	0°	12°
M	0.150 REF		0.006 REF	

PPAK3X3 Dual RECOMMENDED LAND PATTERN



unit : mm